

15 APR 2005

(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property
Organization
International Bureau



(43) International Publication Date
29 April 2004 (29.04.2004)

PCT

(10) International Publication Number
WO 2004/036668 A3

(51) International Patent Classification?: H01M 10/40,
4/04, 4/02, 4/58, C25D 9/04

(21) International Application Number:
PCT/IL2003/000623

(22) International Filing Date: 29 July 2003 (29.07.2003)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
60/418,718 17 October 2002 (17.10.2002) US

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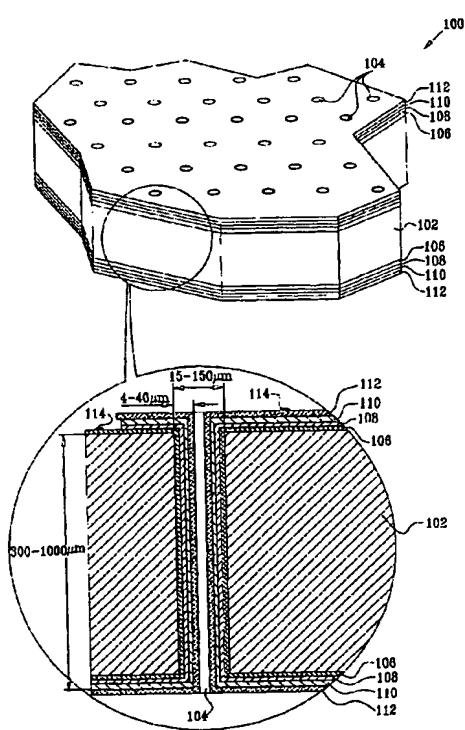
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(81) Designated States (national): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, ES, FI, GB, GD, GE, GH, GM, IR, IL, ID, IN, IS, JP, KE, KG, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NI, NO, NZ, OM, PG, PII, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.

(84) Designated States (regional): ARIPO patent (GH, GM, KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM).

[Continued on next page]

(54) Title: THIN-FILM CATHODE FOR 3-DIMENSIONAL MICROBATTERY AND METHOD FOR PREPARING SUCH CATHODE



(57) Abstract: A method for producing a microbattery (100) including providing a conductive substrate (102), forming a thin film cathodic layer (108) on at least one surface of the conductive substrate, subsequently forming a thin film electrolyte layer (110) over the cathodic layer and subsequently forming a thin film anodic layer (112) over the electrolyte layer.

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European patent (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PT, RO, SE, SI, SK, TR), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NF, SN, TD, TG).

(88) Date of publication of the International search report:
29 December 2004

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.

Published:

- *with international search report*
- *before the expiration of the time limit for amending the claims and to be republished in the event of receipt of amendments*

INTERNATIONAL SEARCH REPORT

International Application No
PCT/IL 03/00623

A. CLASSIFICATION OF SUBJECT MATTER
IPC 7 H01M10/40 H01M4/04 H01M4/02 H01M4/58 C25D9/04

According to International Patent Classification (IPC) or to both national classification and IPC

B. FIELDS SEARCHED

Minimum documentation searched (classification system followed by classification symbols)
IPC 7 H01M C25D

Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched

Electronic data base consulted during the International search (name of data base and, where practical, search terms used)

EPO-Internal, WPI Data, PAJ

C. DOCUMENTS CONSIDERED TO BE RELEVANT

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Further documents are listed in the continuation of box C.

Patent family members are listed in annex.

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Date of the actual completion of the International search

22 November 2004

Date of mailing of the International search report

29/11/2004

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INTERNATIONAL SEARCH REPORT

International Application No
PCT/IL 03/00623

C.(Continuation) DOCUMENTS CONSIDERED TO BE RELEVANT

Category	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
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